

μ PA2463T1Q

MOS FIELD EFFECT TRANSISTOR

R07DS0188EJ0100 Rev.1.00 Dec 06, 2010

Description

The μ PA2463T1Q is a switching device, which can be driven directly by a 2.5 V power source.

The μ PA2463T1Q features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- 2.5 V drive available
- Low on-state resistance
 - --- $R_{DS(on)1} = 20.0 \text{ m}\Omega$ MAX. ($V_{GS} = 4.5 \text{ V}$, $I_D = 3.0 \text{ A}$)
 - --- $R_{DS(on)2}$ = 21.0 mΩ MAX. (V_{GS} = 4.0 V, I_D = 3.0 A)
 - $R_{DS(on)3} = 24.0 \text{ m}\Omega \text{ MAX}.$ ($V_{GS} = 3.1 \text{ V}, I_D = 3.0 \text{ A}$)
 - $R_{DS(on)4} = 28.5 \text{ m}\Omega \text{ MAX}. (V_{GS} = 2.5 \text{ V}, I_D = 3.0 \text{ A})$
- Built-in G-S protection diode against ESD

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μ PA2463T1Q-E1-AX *1	Ni/Pd/Au	8 mm embossed taping	8-pin HUSON (2720)
		3000 p/reel	

Note: *1. Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	N-CHANNEL	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±12	V
Drain Current (DC) *1	I _{D(DC)}	±6	Α
Drain Current (pulse) *2	I _{D(pulse)}	±50	Α
Total Power Dissipation (2 unit) *1	P _{T1}	1.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Notes: *1. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

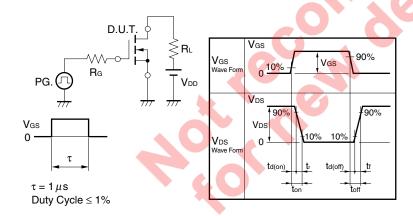
^{*2.} PW \leq 10 μ s, Duty Cycle \leq 1%

Electrical Characteristics ($T_A = 25^{\circ}C$)

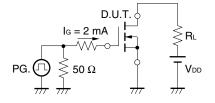
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μΑ	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			±10	μΑ	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$
Gate to Source Cut-off Voltage	$V_{GS(off)}$	0.5	1.0	1.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	2.5			S	$V_{DS} = 10 \text{ V}, I_{D} = 3.0 \text{ A}$
Drain to Source On-state	R _{DS(on)1}	12	16.5	20	mΩ	$V_{GS} = 4.5 \text{ V}, I_D = 3.0 \text{ A}$
Resistance *1	R _{DS(on)2}	13	17	21	mΩ	$V_{GS} = 4.0 \text{ V}, I_D = 3.0 \text{ A}$
	R _{DS(on)3}	13.5	19	24	mΩ	$V_{GS} = 3.1 \text{ V}, I_D = 3.0 \text{ A}$
	R _{DS(on)4}	15	22	28.5	mΩ	$V_{GS} = 2.5 \text{ V}, I_D = 3.0 \text{ A}$
Input Capacitance	C _{iss}		680		pF	V _{DS} = 10 V,
Output Capacitance	Coss		91		pF	$V_{GS} = 0 V$,
Reverse Transfer Capacitance	C _{rss}		70		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		3		μs	$V_{DD} = 10 \text{ V}, I_D = 3.0 \text{ A},$
Rise Time	t _r		6		μs	$V_{GS} = 4 V$,
Turn-off Delay Time	t _{d(off)}		13.5		μs	$R_G = 6 \Omega$
Fall Time	t _f		10		μs	
Total Gate Charge	Q_G		7		nC	V _{DD} = 16 V,
Gate to Source Charge	Q_{GS}		1.3		nC	$V_{GS} = 4 V$,
Gate to Drain Charge	Q_{GD}		2.7		nC	I _D = 6.0 A
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.83		V	I _F = 6.0 A, V _{GS} = 0 V

Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME



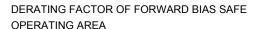
TEST CIRCUIT 2 GATE CHARGE

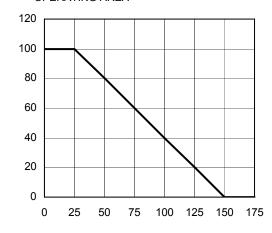


dT - Percentage of Rated Power - %

I_D - Drain Current - A

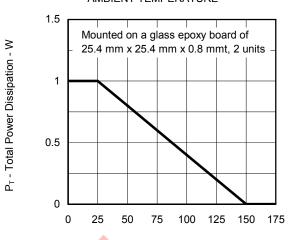
Typical Characteristics (T_A = 25°C)





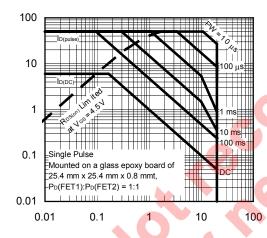
T_A - Ambient Temperature - °C

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



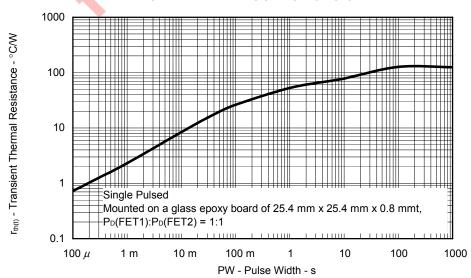
T_A - Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA



V_{DS} - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



I_D - Drain Current - A

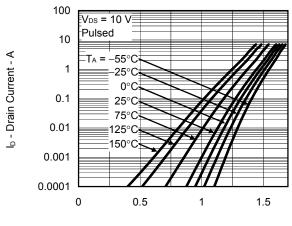
V_{GS(off)} - Gate to Source Cut-off Voltage - V

 $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$



70 60 V_{GS} = 4.5 V 50 4.0 V 40 3.1 V 30 2.5 V 20 10 Pulsed 0 0 0.5 1 1.5 2 2.5 3

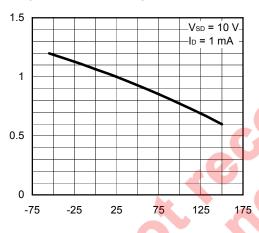
FORWARD TRANSFER CHARACTERISTICS



V_{GS} - Gate to Source Voltage - V

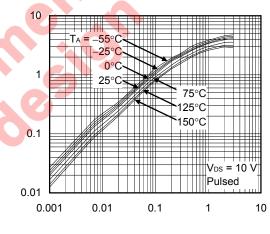
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

 V_{DS} - Drain to Source Voltage - V



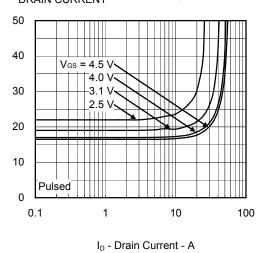
T_{ch} - Channel Temperature - °C

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

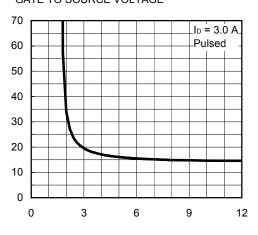


I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



V_{GS} - Gate to Source Voltage - V

 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - $m\Omega$

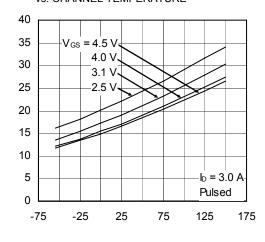
y_s | - Forward Transfer Admittance - S

 $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$

td(on), tr, td(off), tr - Switching Time - µ s

I_F - Diode Forward Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



T_{ch} - Channel Temperature - $^{\circ}C$

0.1

1

V_{DS} - Drain to Source Voltage - V

0.01

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

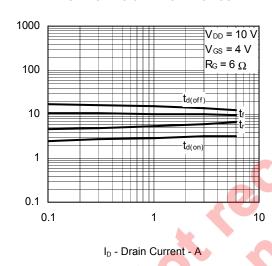
V_{DS} - Drain to Source Voltage - V

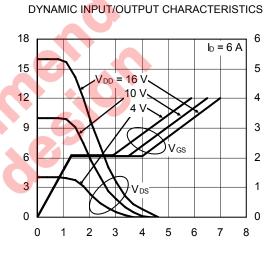
1

10

100

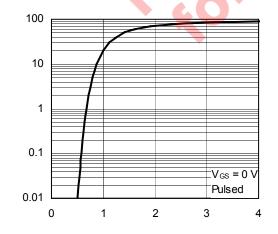
SWITCHING CHARACTERISTICS





Q_G - Gate Charge - nC

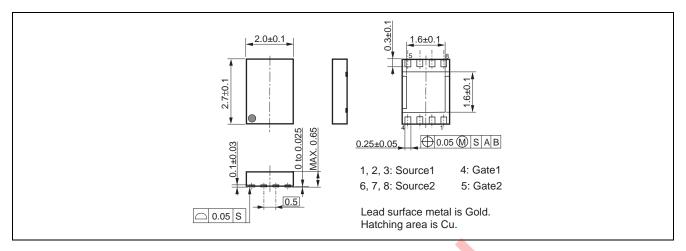
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



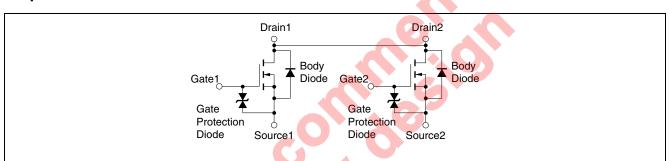
 $V_{F(S-D)}$ - Source to Drain Voltage - V

Package Drawings (Unit: mm)

8-pin HUSON (2720)



Equivalent Circuit



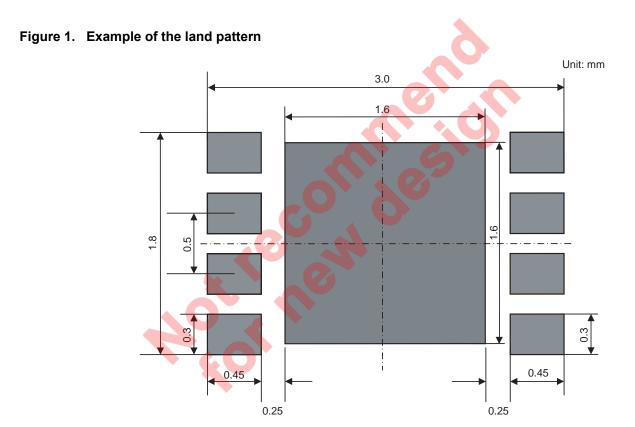
Remark

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

<Notes for using this device safely>

When you use this device, in order to prevent a customer's hazard and damage, use it with understanding the following contents. If used exceeding recommended conditions, there is a possibility of causing failure of the device and characteristic degradation.

- 1. When you mount the device on a substrate, carry out within our recommended soldering conditions of infrared reflow. If mounted exceeding the conditions, the characteristic of a device may be degraded and it may result in failure.
- 2. When you wash the device mounted the substrate, carry out within our recommended conditions. If washed exceeding the conditions, the characteristic of a device may be degraded and it may result in failure.
- 3. When you use ultrasonic wave to substrate after the device mounting, prevent from touching a resonance generator directly. If it touches, the characteristic of a device may be degraded and it may result in failure.
- 4. Please refer to **Figure 1** as an example of the land pattern. Optimize the land pattern in consideration of density, appearance of solder fillets, common difference, etc in an actual design.



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μPA2463T1Q Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Dec 06, 2010	_	First Edition Issued	



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